

	Hit s	Search Text	DBs
1	2	((resist or photoresist or photolithograph\$5 or lithograph\$5) same (mask or pattern) same lift\$4off) and (MR or GMR or (spin near6 valve) or (magnetic near9 head) or read\$6head) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch\$4 or irradiat\$4 or harden\$6 or cur\$4)) and ((resist or photoresist) same ozone same lift\$4off)	US-PPGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
2	6	((resist or photoresist or photolithograph\$5 or lithograph\$5) same (mask or pattern) same lift\$4off) and (MR or GMR or (spin near6 valve) or (magnetic near9 head) or read\$6head) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch\$4 or irradiat\$4 or harden\$6 or cur\$4)) and ((resist or photoresist) same ozone)	US-PPGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
3	0	((resist or photoresist or photolithograph\$5 or lithograph\$5) same (mask or pattern) same lift\$4off) and (MR or GMR or (spin near6 valve) or (magnetic near9 head) or read\$6head) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch\$4 or irradiat\$4 or harden\$6 or cur\$4)) and ((resist or photoresist) same (oxidation or ozone or oxidati\$4) same treat\$5 same lift\$5off)	US-PPGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
4	5	((resist or photoresist or photolithograph\$5 or lithograph\$5) same (mask or pattern) same lift\$4off) and (MR or GMR or (spin near6 valve) or (magnetic near9 head) or read\$6head) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch\$4 or irradiat\$4 or harden\$6 or cur\$4)) and ((resist or photoresist) same (oxidation or ozone or oxidati\$4) same treat\$5)	US-PPGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
5	15	((resist or photoresist or photolithograph\$5 or lithograph\$5) same (mask or pattern) same lift\$4off) and (MR or GMR or (spin near6 valve) or (magnetic near9 head) or read\$6head) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch\$4 or irradiat\$4 or harden\$6 or cur\$4)) and ((resist or photoresist) same (oxidation or ozone or oxidi\$4)) and ((resist or photoresist) same (mask or pattern\$4) same (sputter\$4 or deposit\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
6	2	((resist or photoresist or photolithograph\$5 or lithograph\$5) same (mask or pattern) same lift\$4off) and (MR or GMR or (spin near6 valve) or (magnetic near9 head) or read\$6head) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch\$4 or irradiat\$4 or harden\$6 or cur\$4)) and ((resist or photoresist) same (oxidation or ozone or oxidi\$4)) and ((resist or photoresist) same (mask or pattern\$4) same (sputter\$4 or deposit\$4 or coat\$4 or layer or form\$4)) and ((ion near9 (beam or gun or source)) same (voltage or volt)) and ((resist or photoresist) same (thickness or thick\$4 or nm))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
7	2	((resist or photoresist or photolithograph\$5 or lithograph\$5) same (mask or pattern) same lift\$4off) and (MR or GMR or (spin near6 valve) or (magnetic near9 head) or read\$6head) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch\$4 or irradiat\$4 or harden\$6 or cur\$4)) and ((resist or photoresist) same (oxidation or ozone or oxidi\$4 or passivat\$5)) and ((ion near9 (beam or gun or source)) same (voltage or volt)) and ((resist or photoresist) same (thickness or thick\$4 or nm))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
8	24	((resist or photoresist or photolithograph\$5 or lithograph\$5) same (mask or pattern) same lift\$4off) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch\$4 or irradiat\$4 or harden\$6 or cur\$4)) and ((resist or photoresist) same (oxidation or ozone or oxidi\$4 or passivat\$5)) and ((ion near9 (beam or gun or source)) same (voltage or volt)) and ((resist or photoresist) same (thickness or thick\$4 or nm))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
9	22	S8 NOT S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
10	46	((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch\$4 or irradiat\$4 or harden\$6 or cur\$4)) and ((resist or photoresist) same (oxidation or ozone or oxidi\$4 or passivat\$5) same (plasma or ion\$4beam)) and ((ion near9 (beam or gun or source)) same (voltage or volt)) and ((resist or photoresist) same (thickness or thick\$4 or nm))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
11	15	((resist or photoresist or photolithograph\$5 or lithograph\$5) same (mask or pattern) same lift\$4off) and (MR or GMR or (spin near6 valve) or (magnetic near9 head) or read\$6head) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch\$4 or irradiat\$4 or harden\$6 or cur\$4)) and ((resist or photoresist) same (oxidation or ozone or oxidi\$4)) and ((resist or photoresist) same (mask or pattern\$4) same (sputter\$4 or deposit\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
12	24	((resist or photoresist or photolithograph\$5 or lithograph\$5) same (mask or pattern) same lift\$4off) and ((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (etch\$4 or irradiat\$4 or harden\$6 or cur\$4)) and ((resist or photoresist) same (oxidation or ozone or oxidi\$4 or passivat\$5)) and ((ion near9 (beam or gun or source)) same (voltage or volt)) and ((resist or photoresist) same (thickness or thick\$4 or nm))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
13	22	S12 NOT S11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
14	37	S10 NOT S13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
15	5	((resist or photoresist) same (pattern or mask) same (ion near9 (beam or gun or source)) same (expos\$4 or irradiat\$4 or harden\$6 or cur\$4)) and ((resist or photoresist or pattern) same ozone same (plasma or ion\$4beam or treat\$4 or passivat\$)) and ((resist or photoresist) same (mask or pattern) same ((bottom near9 width) or (bottom near9 portion) or undercut\$4 or shadow\$4 or overhang\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
16	12	((resist or photoresist or photolithograph\$5 or lithograph\$5) near14 (mask or pattern) near28 lift\$4off near22 (thickness or thick) near29 (overhang or undercut or shadow))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
17	6	((resist or photoresist or photolithograph\$5 or lithograph\$5) same (mask or pattern) same lift\$4off same (overhang or undercut or shadow) same (ion\$5beam or (ion2 near9 expos\$4)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
18	1	((resist or photoresist) near14 (mask or pattern) near26 ((ion near5 beam) or (ion near6 expos\$4)) near26 volt\$4) same lift\$5off)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
19	18	((resist or photoresist or photolithograph\$5 or lithograph\$5) same (mask or pattern) same lift\$4off same ozone)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
20	31	((resist or photoresist or photolithograph\$5 or lithograph\$5) same (mask or pattern) same ozone) and (lift\$5off same (resist or photoresist or mask or pattern))	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
21	13	S23 NOT S22	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
22	15	((resist or photoresist or photolithograph\$5 or lithograph\$5) same (mask or pattern) same ozone same treat\$4) and lift\$5off and ((plasma or irradiat\$4 or expos\$\$ or illuminat\$4) same (oxygen or ozone))	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
23	4	((resist or photoresist or photolithograph\$5 or lithograph\$5) same (mask or pattern) same ozone same treat\$4) and lift\$5off and ((plasma or irradiat\$4 or expos\$\$ or illuminat\$4) same (oxygen or ozone)) and (((flow near12 rate) or rate) same ozone)	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
24	26	((resist or photoresist) same ozone same treat\$4) and lift\$5off and ((plasma or irradiat\$4 or expos\$4 or illuminat\$4) same (oxygen or ozone))	US - PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hit s	Search Text	DBs
25	2	((resist or photoresist) same oxid\$5 same treat\$4) and lift\$5off and ((plasma or irradiat\$4 or expos\$4 or illuminat\$4) same (oxygen or ozone)) and (develop\$4 same (NMP or (methyl near5 pyrrolidone)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB